Vicente MuÃ±oz-Sanjose

List of Publications by Year
in descending order

220 papers	4,803 citations	108046 37 h-index	156644 58 g-index
222 all docs	222 docs citations	222 times ranked	6316 citing authors

#	Article	IF	Citations
1	White light emission from lead-free mixed-cation doped Cs₂SnCl₆ nanocrystals. Nanoscale, 2022, 14, 1468-1479.	2.8	29
2	Coupling of localized surface plasmons to intersubband transitions in CdO/GaAs. , 2022, , .		0
3	Local structure in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.svg"><mml:mrow><mml:mi>G</mml:mi><mml:msub><mml:mi>a</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo alloys. Journal of Alloys and Compounds, 2021, 852, 156365.	2.8	4
4	Engineering Sr-doping for enabling long-term stable FAPb_{1â^’x}Sr_xI₃ quantum dots with 100% photoluminescence quantum yield. Journal of Materials Chemistry C, 2021, 9, 1555-1566.	2.7	23
5	High Optical Performance of Cyanâ€Emissive CsPbBr₃ Perovskite Quantum Dots Embedded in Molecular Organogels. Advanced Optical Materials, 2021, 9, 2001786.	3.6	10
6	Self-assembled metal-oxide nanoparticles on GaAs: infrared absorption enabled by localized surface plasmons. Nanophotonics, 2021, 10, 2509-2518.	2.9	6
7	Plasmonic CdZnO nanoparticles for enhanced GaAs-based quantum well intersubband absorption. , 2021, , .		0
8	Morphology and Band Structure of Orthorhombic PbS Nanoplatelets: An Indirect Band Gap Material. Chemistry of Materials, 2021, 33, 420-429.	3.2	7
9	Induced crystallographic changes in Cd1â^’xZnxO films grown on r-sapphire by AP-MOCVD: the effects of the Zn content when x â‰ 0.5. CrystEngComm, 2020, 22, 74-84.	1.3	2
10	Unravelling the Photocatalytic Behavior of All-Inorganic Mixed Halide Perovskites: The Role of Surface Chemical States. ACS Applied Materials & Interfaces, 2020, 12, 914-924.	4.0	55
11	Preferred Growth Direction by PbS Nanoplatelets Preserves Perovskite Infrared Light Harvesting for Stable, Reproducible, and Efficient Solar Cells. Advanced Energy Materials, 2020, 10, 2002422.	10.2	20
12	Controllable and Highly Propagative Hybrid Surface Plasmonâ€“Phonon Polariton in a CdZnO-Based Two-Interface System. ACS Photonics, 2019, 6, 2816-2822.	3.2	10
13	Structural and morphological characterization of the Cd-rich region in Cd1-xZnxO thin films grown by atmospheric pressure metal organic chemical vapour deposition. Thin Solid Films, 2019, 683, 128-134.	0.8	5
14	Correlative study of structural and optical properties of ZnSe under severe plastic deformation. Journal of Applied Physics, 2019, 126, 225702.	1.1	6
15	Controlling the Phase Segregation in Mixed Halide Perovskites through Nanocrystal Size. ACS Energy Letters, 2019, 4, 54-62.	8.8	149
16	Study of the Partial Substitution of Pb by Sn in Csâ€“Pbâ€“Snâ€“Br Nanocrystals Owing to Obtaining Stable Nanoparticles with Excellent Optical Properties. Journal of Physical Chemistry C, 2018, 122, 14222-14231.	1.5	38
17	Rock-salt CdZnO as a transparent conductive oxide. Applied Physics Letters, 2018, 113, .	1.5	17
18	Phase segregation in MgxZn1â€“xO probed by optical absorption and photoluminescence at high pressure. Journal of Applied Physics, 2017, 122, 105902.	1.1	0

#	Article	IF	Citations
19	Effect of Growth Temperature on the Structural and Morphological Properties of MgCdO Thin Films Grown by Metal Organic Chemical Vapor Deposition. Crystal Growth and Design, 2017, 17, 6303-6310.	1.4	11
20	Sensing properties of ZnO nanostructured layers. , 2017, , .		0
21	Hybrid multiple diffraction in semipolar wurtzite materials: (f 01overline{1}2)-oriented ZnMgO/ZnO heterostructures as an illustration. Journal of Applied Crystallography, 2017, 50, 1165-1173.	1.9	3
22	Growth and characterization of Mg_{1â€x}Cd_xO thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 452-455.	0.8	6
23	Gas-phase supersaturation effects on morphology properties of ZnO nano and microstructures grown by PVT. Journal of Physics: Conference Series, 2016, 687, 012027.	0.3	2
24	Observation of a charge delocalization from Se vacancies in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Bi</mml:mi><mml:mn>2</mml:mn></mml:m A positron annihilation study of native defects. Physical Review B, 2016, 94, .	2.1	5
25	SubstructuralÂProperties and Anisotropic Peak Broadening in Zn1â^'x Mn x Te Films Determined by a Combined Methodology Based on SEM, HRTEM, XRD, and HRXRD. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2016, 47, 6645-6654.	1.1	2
26	Publisher's Note: Observation of a charge delocalization from Se vacancies inBi2Se3: A positron annihilation study of native defects [Phys. Rev. B 94, 014117 (2016)]. Physical Review B, 2016, 94, .	1.1	0
27	ZnMgO-based UV photodiodes: a comparison of films grown by spray pyrolysis and MBE. , 2016, , .		4
28	MOCVD growth of CdO very thin films: Problems and ways of solution. Applied Surface Science, 2016, 385, 209-215.	3.1	8
29	Optical properties of ZnMgO films grown by spray pyrolysis and their application to UV photodetection. Semiconductor Science and Technology, 2015, 30, 105026.	1.0	9
30	Growth of tin oxide thin films composed of nanoparticles on hydrophilic and hydrophobic glass substrates by spray pyrolysis technique. Applied Surface Science, 2015, 357, 915-921.	3.1	8
31	Quenching and blue shift of UV emission intensity of hydrothermally grown ZnO:Mn nanorods. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 191, 1-6.	1.7	17
32	Hard x-ray photoelectron spectroscopy as a probe of the intrinsic electronic properties of CdO. Physical Review B, 2014, 89, .	1.1	28
33	Photoluminescence in ZnO:Co²⁺ (0.01%â€“5%) Nanoparticles, Nanowires, Thin Films, and Single Crystals as a Function of Pressure and Temperature: Exploring Electronâ€“Phonon Interactions. Chemistry of Materials, 2014, 26, 1100-1107.	3.2	19
34	One-step growth of isolated CdO nanoparticles on r-sapphire substrates by using the spray pyrolysis methodology. RSC Advances, 2014, 4, 23137.	1.7	12
35	Valence-band orbital character of CdO: A synchrotron-radiation photoelectron spectroscopy and density functional theory study. Physical Review B, 2014, 89, .	1.1	38
36	Growth and characterization of self-assembled Cd_{1â^'x}Mg_xO (0 â‰ x â‰ 1) nanoparticles on r-sapphire substrates. CrystEngComm, 2014, 16, 8969-8976.	1.3	4

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37	VIS-UV ZnCdO/ZnO multiple quantum well nanowires and the quantification of Cd diffusion. Nanotechnology, 2014, 25, 255202.	1.3	11
38	Mn²⁺â€induced roomâ€temperature ferromagnetism and spinâ€glass behavior in hydrothermally grown Mnâ€doped ZnO nanorods. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1155-1161.	0.8	17
39	Optical properties and microstructure of 2.02-3.30 eV ZnCdO nanowires: Effect of thermal annealing. Applied Physics Letters, 2013, 102, .	1.5	15
40	Temperature dependence of the direct bandgap and transport properties of CdO. Applied Physics Letters, 2013, 102, .	1.5	68
41	Self-assembled MgxZn_{1âˆ’x}O quantum dots (0 â‰ x â‰ 1) on different substrates using spray pyrolysis methodology. CrystEngComm, 2013, 15, 182-191.	1.3	11
42	Influence of metal organic chemical vapour deposition growth conditions on vibrational and luminescent properties of ZnO nanorods. Journal of Applied Physics, 2013, 113, .	1.1	11
43	On the interplay of point defects and Cd in non-polar ZnCdO films. Journal of Applied Physics, 2013, 113, 023512.	1.1	7
44	Assessment of the out-plane and in-plane ordering of high quality ZnO nanorods by X-ray multiple diffraction. Thin Solid Films, 2013, 541, 107-112.	0.8	3
45	Non-radiative recombination centres in catalyst-free ZnO nanorods grown by atmospheric-metal organic chemical vapour deposition. Journal Physics D: Applied Physics, 2013, 46, 235302.	1.3	101
46	High-pressure Raman scattering of CdO thin films grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2013, 113, .	1.1	23
47	High resolution X-ray diffraction, X-ray multiple diffraction and cathodoluminescence as combined tools for the characterization of substrates for epitaxy: the ZnO case. CrystEngComm, 2013, 15, 3951.	1.3	3
48	Non radiative recombination centers in ZnO nanorods. Materials Research Society Symposia Proceedings, 2013, 1538, 317-322.	0.1	2
49	Highâ€pressure studies of topological insulators Bi₂Se₃, Bi₂Te₃, and Sb₂Te₃. Physica Status Solidi (B): Basic Research, 2013, 250, 669-676.	0.7	77
50	Temperature-dependent optical properties of epitaxial CdO thin films determined by spectroscopic ellipsometry and Raman scattering. Journal of Applied Physics, 2013, 113, 183515.	1.1	11
51	Trapping of three-dimensional electrons and transition to two-dimensional transport in the three-dimensional topological insulator Bi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Se<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>under high pressure. Physical Review B, 2012, 85, .	1.1	29
52	High resolution x-ray diffraction methodology for the structural analysis of one-dimensional nanostructures. Journal of Applied Physics, 2012, 112, .	1.1	5
53	Morphology transitions in ZnO nanorods grown by MOCVD. Journal of Crystal Growth, 2012, 359, 122-128.	0.7	42
54	Synthesis and Characterization of ZnO Nano and Micro Structures Grown by Low Temperature Spray Pyrolysis and Vapor Transport. Journal of Nanoscience and Nanotechnology, 2012, 12, 6792-6799.	0.9	1

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55	Enhanced UV emission from ZnO nanoflowers synthesized by the hydrothermal process. Journal Physics D: Applied Physics, 2012, 45, 425103.	1.3	38
56	Self-Assembled Zinc Oxide Quantum Dots Using Spray Pyrolysis Methodology. Crystal Growth and Design, 2011, 11, 3790-3801.	1.4	10
57	Structural and vibrational study of Bi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Se<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>under high pressure. Physical Review B, 2011, 84, .	1.1	138
58	Determination of defect content and defect profile in semiconductor heterostructures. Journal of Physics: Conference Series, 2011, 265, 012004.	0.3	1
59	High-pressure vibrational and optical study of Bi<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>Te<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review B, 2011, 84, .	1.1	100
60	Electron mobility in CdO films. Journal of Applied Physics, 2011, 109, .	1.1	51
61	Spray pyrolytic deposition of ZnO thin layers composed of low dimensional nanostructures. Physics Procedia, 2010, 8, 14-17.	1.2	2
62	Crystal growth of ZnO micro and nanostructures by PVT on c-sapphire and amorphous quartz substrates. Physics Procedia, 2010, 8, 121-125.	1.2	1
63	Structural characterization of one-dimensional ZnO-based nanostructures grown by MOCVD. Physica Status Solidi (B): Basic Research, 2010, 247, 1683-1686.	0.7	10
64	Temperature- and illumination-induced charge-state change in divacancies of GaTe. Physical Review B, 2010, 81, .	1.1	1
65	Determination of limiting factors of photovoltaic efficiency in quantum dot sensitized solar cells: Correlation between cell performance and structural properties. Journal of Applied Physics, 2010, 108, 064310.	1.1	42
66	Anharmonic effects in ZnO optical phonons probed by Raman spectroscopy. Applied Physics Letters, 2010, 96, .	1.5	35
67	Surface Band-Gap Narrowing in Quantized Electron Accumulation Layers. Physical Review Letters, 2010, 104, 256803.	2.9	86
68	Ellipsometric study of single-crystal Î³-InSe from 1.5 to 9.2 eV. Applied Physics Letters, 2010, 96, 181902.	1.5	13
69	Raman scattering of cadmium oxide epilayers grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2010, 107, .	1.1	64
70	Complex dielectric function and refractive index spectra of epitaxial CdO thin film grown on r-plane sapphire from 0.74 to 6.45 eV. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 1120-1124.	0.6	21
71	Unification of the electrical behavior of defects, impurities, and surface states in semiconductors: Virtual gap states in CdO. Physical Review B, 2009, 79, .	1.1	76
72	ZnO films grown by MOCVD on GaAs substrates: Effects of a Zn buffer deposition on interface, structural and morphological properties. Journal of Crystal Growth, 2009, 311, 2564-2571.	0.7	4

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73	Above-bandgap ordinary optical properties of GaSe single crystal. Journal of Applied Physics, 2009, 106, .	1.1	31
74	Valence-band electronic structure of CdO, ZnO, and MgO from x-ray photoemission spectroscopy and quasi-particle-corrected density-functional theory calculations. Physical Review B, 2009, 79, .	1.1	124
75	Anisotropic chemical etching of semipolar {10ar {1}ar {1}}mbox {/} {10ar {1}{+}1} ZnO crystallographic planes: polarity versus dangling bonds. Nanotechnology, 2009, 20, 065701.	1.3	11
76	Hall-effect and resistivity measurements in CdTe and ZnTe at high pressure: Electronic structure of impurities in the zinc-blende phase and the semimetallic or metallic character of the high-pressure phases. Physical Review B, 2009, 79, .	1.1	54
77	Growth and characterization of GdxHg1â^'xSe crystals. Journal of Crystal Growth, 2008, 310, 3752-3757.	0.7	0
78	Bandgap and effective mass of epitaxial cadmium oxide. Applied Physics Letters, 2008, 92, .	1.5	158
79	Thermal Creation of Defects in GaTe. Japanese Journal of Applied Physics, 2008, 47, 8719-8722.	0.8	1
80	Response to â€œComment on â€˜Bandgap and effective mass determination of epitaxial cadmium oxideâ€™â€• [Appl. Phys. Lett. 92, 106103 (2008)]. Applied Physics Letters, 2008, 92, 106104.	1.5	2
81	Observation of quantized subband states and evidence for surface electron accumulation in CdO from angle-resolved photoemission spectroscopy. Physical Review B, 2008, 78, .	1.1	75
82	Electronic structure of single-crystal rocksalt CdO studied by soft x-ray spectroscopies and<i>ab initio</i>calculations. Physical Review B, 2008, 77, .	1.1	35
83	Characterization of Non-Polar ZnO Layers with Positron Annihilation Spectroscopy. Acta Physica Polonica A, 2008, 114, 1257-1264.	0.2	6
84	Structural and Optical Properties of Zn(1-x)CdxO Solid Solutions Grown on ZnO Substrates by Using MO-CVD. Journal of the Korean Physical Society, 2008, 53, 158-162.	0.3	4
85	Ab-Initio Studies of Electronic and Spectroscopic Properties of MgO, ZnO and CdO. Journal of the Korean Physical Society, 2008, 53, 2811-2815.	0.3	26
86	Positron annihilation spectroscopy for the determination of thickness and defect profile in thin semiconductor layers. Physical Review B, 2007, 75, .	1.1	28
87	Structural and morphological characterizations of ZnO films grown on GaAs substrates by MOCVD. Applied Physics A: Materials Science and Processing, 2007, 88, 83-87.	1.1	7
88	Formation and Rupture of Schottky Nanocontacts on ZnO Nanocolumns. Nano Letters, 2007, 7, 1505-1511.	4.5	54
89	Positron annihilation lifetime spectroscopy of ZnO bulk samples. Physical Review B, 2007, 76, .	1.1	47
90	Study of the MOCVD growth of ZnO on GaAs substrates: Influence of the molar ratio of the precursors on structural and morphological properties. Superlattices and Microstructures, 2007, 42, 140-144.	1.4	2

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91	Crystal growth of Hg1âˆ’xMnxSe for infrared detection. Microelectronics Journal, 2007, 38, 327-331.	1.1	4
92	New method for the determination of the defect profile in thin layers grown over a substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3973-3976.	0.8	1
93	Nanogoniometry with Scanning Force Microscopy: A Model Study of CdTe Thin Films. Small, 2007, 3, 474-480.	5.2	5
94	Nanoscale determination of surface orientation and electrostatic properties of ZnO thin films. Applied Physics A: Materials Science and Processing, 2007, 88, 77-82.	1.1	7
95	Properties of the oxygen vacancy in ZnO. Applied Physics A: Materials Science and Processing, 2007, 88, 147-151.	1.1	153
96	Energetically deep defect centers in vapor-phase grown zinc oxide. Applied Physics A: Materials Science and Processing, 2007, 88, 141-145.	1.1	47
97	X-ray and transmission electron microscopy characterization of twinned CdO thin films grown on a-plane sapphire by metalorganic vapour phase epitaxy. Applied Physics A: Materials Science and Processing, 2007, 88, 61-64.	1.1	0
98	X-ray photoemission studies of the electronic structure of single-crystalline CdO(100). Superlattices and Microstructures, 2007, 42, 197-200.	1.4	20
99	Structural characterization of a-plane Zn1âˆ’xCdxO (0â©½xâ©½0.085) thin films grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2006, 99, 023514.	1.1	61
100	Optical active centres in ZnO samples. Journal of Non-Crystalline Solids, 2006, 352, 1453-1456.	1.5	18
101	Luminescence and structural properties of defects in ion implanted ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 968-971.	0.8	9
102	Negative U-properties of the oxygen-vacancy in ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 997-1000.	0.8	11
103	Twin coarsening in CdTe(111) films grown on GaAs(100). Acta Materialia, 2006, 54, 4285-4291.	3.8	14
104	High-pressure electrical transport measurements on p-type GaSe and InSe. High Pressure Research, 2006, 26, 513-516.	0.4	33
105	Intrinsic and extrinsic point-defects in vapor transport grown ZnO bulk crystals. Physica B: Condensed Matter, 2006, 376-377, 767-770.	1.3	11
106	Growth of ZnO crystals by vapour transport: Some ways to act on physical properties. Crystal Research and Technology, 2006, 41, 742-747.	0.6	11
107	Facets evolution and surface electrical properties of nonpolar m-plane ZnO thin films. Applied Physics Letters, 2006, 88, 261912.	1.5	45
108	Correlation between Zn vacancies and photoluminescence emission in ZnO films. Journal of Applied Physics, 2006, 99, 053516.	1.1	46

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109	Quantum dots of Cd0.5Mn0.5Te semimagnetic semiconductor formed by the cold isostatic pressure method. Journal of Magnetism and Magnetic Materials, 2005, 294, e77-e81.	1.0	0
110	ZnO/CdTe/CuSCN, a promising heterostructure to act as inorganic eta-solar cell. Thin Solid Films, 2005, 483, 372-377.	0.8	87
111	A new approach to the growth of ZnO by vapour transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1106-1114.	0.8	10
112	X-ray characterization of CdO thin films grown ona-,c-,r- andm-plane sapphire by metalorganic vapour phase-epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1233-1238.	0.8	14
113	High-pressure phase diagram ofZnSexTe1â[^]'xalloys. Physical Review B, 2005, 71, .	1.1	14
114	Faceting and structural anisotropy of nanopatterned CdO(110) layers. Journal of Applied Physics, 2005, 98, 034311.	1.1	3
115	Zinc vacancies in the heteroepitaxy of ZnO on sapphire: Influence of the substrate orientation and layer thickness. Applied Physics Letters, 2005, 86, 042103.	1.5	57
116	IIâ€"VI and II1â^'xMnxVI semiconductor nanocrystals formed by the pressure cycle method. High Pressure Research, 2005, 25, 119-135.	0.4	2
117	Polarity Effects on ZnO Films Grown along the Nonpolar[112Â¯0]Direction. Physical Review Letters, 2005, 95, 226105.	2.9	63
118	The Scope of Zinc Oxide Bulk Growth. , 2005, , 3-14.		1
119	X-ray-absorption fine-structure study of ZnSexTe1â^'x alloys. Journal of Applied Physics, 2004, 96, 1491-1498.	1.1	23
120	Band structure of indium selenide investigated by intrinsic photoluminescence under high pressure. Physical Review B, 2004, 70, .	1.1	35
121	Semiconductor-metal transitions in liquidIn100â^'xSexalloys: A concentration-induced transition. Physical Review B, 2004, 69, .	1.1	6
122	MOCVD growth of CdTe on glass: analysis of in situ post-growth annealing. Journal of Crystal Growth, 2004, 262, 19-27.	0.7	18
123	Morphology of ZnO grown by MOCVD on sapphire substrates. Journal of Crystal Growth, 2004, 264, 70-78.	0.7	39
124	Structural characterization of CdTe layers grown on (0001) sapphire by MOCVD. Journal of Crystal Growth, 2004, 270, 309-315.	0.7	15
125	Effect of structural and compositional inhomogeneities on spin-glass transition in Hg1â^'xâ^'yCrxMnySe crystals. Journal of Crystal Growth, 2004, 262, 403-407.	0.7	3
126	Numerical study of the ZnO growth by MOCVD. Journal of Crystal Growth, 2004, 264, 237-245.	0.7	14

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127	Study of the ZnO crystal growth by vapour transport methods. Journal of Crystal Growth, 2004, 270, 711-721.	0.7	26
128	Structural analysis of CdO layers grown on r-plane sapphire <mml:math altimg="si1.gif" overflow="scroll" xmlns:xocs="http://www.elsevier.com/xml/xocs/dtd" xmlns:xs="http://www.w3.org/2001/XMLSchema" xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance" xmlns="http://www.elsevier.com/xml/ja/dtd" xmlns:ja="http://www.elsevier.com/xml/ja/dtd" xmlns:mml="http://www.w3.org/1998/Math/MathML" xmlns:tb="http://www.elsevier.com/xml/common/table/dtd" xmlns:sb="http://www.elsevier.com/xml/co	0.7	36
129	Influence of twinned structure on the morphology of CdTe(111) layers grown by MOCVD on GaAs(100) substrates. Journal of Crystal Growth, 2003, 257, 60-68.	0.7	16
130	Specific features of the electronic structure of IIIâ€“VI layered semiconductors: recent results on structural and optical measurements under pressure and electronic structure calculations. Physica Status Solidi (B): Basic Research, 2003, 235, 267-276.	0.7	26
131	Pressure and temperature dependence of the band-gap in CdTe. Physica Status Solidi (B): Basic Research, 2003, 235, 441-445.	0.7	12
132	Electronic structure and optical properties of CdTe rock-salt high pressure phase. Physica Status Solidi (B): Basic Research, 2003, 235, 509-513.	0.7	8
133	STRUCTURAL CHARACTERIZATION OF THE CINNABAR PHASE IN ZnSexTe1-x ALLOYS. High Pressure Research, 2003, 23, 339-342.	0.4	4
134	Near band edge recombination mechanisms in GaTe. Physical Review B, 2003, 68, .	1.1	24
135	Nanocrystals of cdte formed by the pressure cycle method. High Pressure Research, 2003, 23, 29-33.	0.4	2
136	Crystal Growth of HgSe by the Cold Travelling Heater Method. Crystal Growth and Design, 2002, 2, 91-92.	1.4	11
137	Observation of the Cinnabar Phase in ZnSe at High Pressure. High Pressure Research, 2002, 22, 355-359.	0.4	6
138	Angle-resolved photoemission study and first-principles calculation of the electronic structure of GaTe. Physical Review B, 2002, 65, .	1.1	38
139	Pressure Dependence of the Bandgap Bowing in Zinc-Blende ZnTe 1âˆ’ x Se x. High Pressure Research, 2002, 22, 257-260.	0.4	5
140	Recombination processes in unintentionally doped GaTe single crystals. Journal of Applied Physics, 2002, 92, 7330-7336.	1.1	21
141	High-pressure x-ray-absorption study of GaSe. Physical Review B, 2002, 65, .	1.1	36
142	Some aspects of the MOCVD growth of ZnO on sapphire using tert-butanol. Materials Letters, 2002, 53, 126-131.	1.3	38
143	Photoluminescence Study of ZnSe Single Crystals Obtained by Solid Phase Recrystallization under Different Pressure Conditions. Effects of Thermal Treatment. Physica Status Solidi A, 2002, 194, 338-348.	1.7	21
144	A new CdTe/ZnO columnar composite film for Eta-solar cells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 14, 229-232.	1.3	66

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145	Surface passivation of gallium selenide by nitrogen implantation. Surface and Interface Analysis, 2002, 34, 460-463.	0.8	6
146	Numerical study of the growth conditions in an MOCVD reactor: application to the epitaxial growth of HgTe. Journal of Crystal Growth, 2002, 240, 124-134.	0.7	6
147	A numerical study of thermal conditions in the THM growth of HgTe. Journal of Crystal Growth, 2002, 243, 463-475.	0.7	13
148	Microstructural characterization of TiB2 armor targets. Journal of Materials Science Letters, 2002, 21, 1661-1666.	0.5	15
149	Experimental and theoretical study of band structure of InSe andIn1â^'xGaxSe(x<0.2)under high pressure:â€,Direct to indirect crossovers. Physical Review B, 2001, 63, .	1.1	73
150	Vapor growth of Hg1â^'xCdxI2 on glass using CdTe buffer. Thin Solid Films, 2001, 381, 48-51.	0.8	5
151	Scanning electron microscopy study of twins in ZnSe single crystals grown by solid-phase recrystallization. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 130-133.	1.7	3
152	CdTe crystal growth process by the Bridgman method: numerical simulation. Journal of Crystal Growth, 2001, 222, 435-451.	0.7	26
153	Growth and characterisation of MnTe crystals. Journal of Crystal Growth, 2001, 223, 349-356.	0.7	24
154	A new approach to the crystal growth of Hg1â^'xMnxTe by the cold travelling heater method (CTHM). Journal of Crystal Growth, 2001, 223, 357-362.	0.7	7
155	Deep center luminescence versus surface preparation of ZnSe single crystals. Journal of Materials Research, 2001, 16, 1245-1248.	1.2	7
156	Cathodoluminescence and photoluminescence study of plastically deformed ZnTe bulk single crystals. Semiconductor Science and Technology, 2001, 16, 289-292.	1.0	4
157	Cinnabar phase in ZnSe at high pressure. Physical Review B, 2001, 65, .	1.1	35
158	Optical Absorption of Zinc Selenide Doped with Cobalt (Zn1-xCoxSe) under Hydrostatic Pressure. Physica Status Solidi A, 2000, 180, 561-568.	1.7	7
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